



TIP122FP TIP127FP

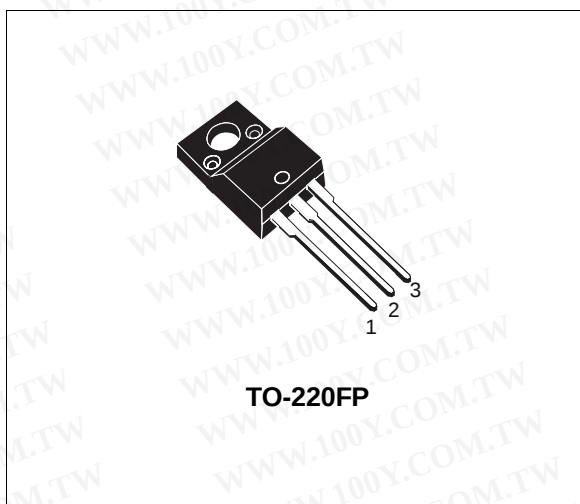
COMPLEMENTARY SILICON POWER DARLINGTON TRANSISTORS

- STMicroelectronics PREFERRED SALESTYPES
- FULLY INSULATED PACKAGE (U.L. COMPLIANT) FOR EASY MOUNTING

DESCRIPTION

The TIP122FP is a silicon Epitaxial-Base NPN power transistor in monolithic Darlington configuration mounted in Jedec TO-220FP fully molded isolated package. It is intended for use in power linear and switching applications.

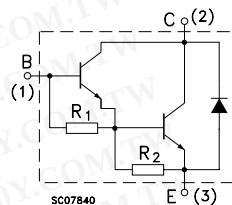
The complementary PNP type is TIP127FP.



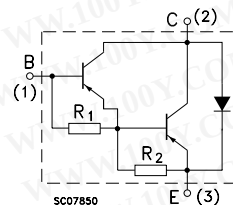
TO-220FP

勝特力材料 886-3-5753170
勝特力电子(上海) 86-21-54151736
勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

INTERNAL SCHEMATIC DIAGRAM



R₁ Typ. = 5 K Ω



R₂ Typ. = 150 Ω

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	NPN	TIP122FP	Unit
		PNP	TIP127FP	
V _{CBO}	Collector-Base Voltage (I _E = 0)		100	V
V _{CEO}	Collector-Emitter Voltage (I _B = 0)		100	V
V _{EBO}	Emitter-Base Voltage (I _C = 0)		5	V
I _C	Collector Current		5	A
I _{CM}	Collector Peak Current (t _p < 5 ms)		8	A
I _B	Base Current		0.1	A
P _{tot}	Total Dissipation at T _{case} $\leq$ 25 $^{\circ}$ C T _{amb} $\leq$ 25 $^{\circ}$ C		29 2	W W
V _{isol}	Insulation Withstand Voltage (RMS) from All Three Leads to External Heatsink		1500	V
T _{stg}	Storage Temperature		-65 to 150	$^{\circ}$ C
T _j	Max. Operating Junction Temperature		150	$^{\circ}$ C

For PNP types voltage and current values are negative.

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THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	4.3	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	62.5	°C/W

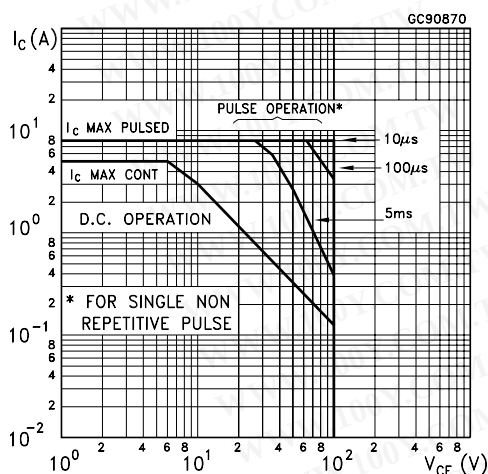
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CEO}	Collector Cut-off Current (I _B = 0)	V _{CE} = 50 V			0.5	mA
I _{CBO}	Collector Cut-off Current (I _E = 0)	V _{CB} = 100 V			0.2	mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			2	mA
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 30 mA	100			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 3 A I _C = 5 A			2 4	V V
V _{BE(on)} *	Base-Emitter Voltage	I _C = 3 A V _{CE} = 3 V			2.5	V
h _{FE} *	DC Current Gain	I _C = 0.5 A I _C = 3 A V _{CE} = 3 V V _{CE} = 3 V	1000 1000			

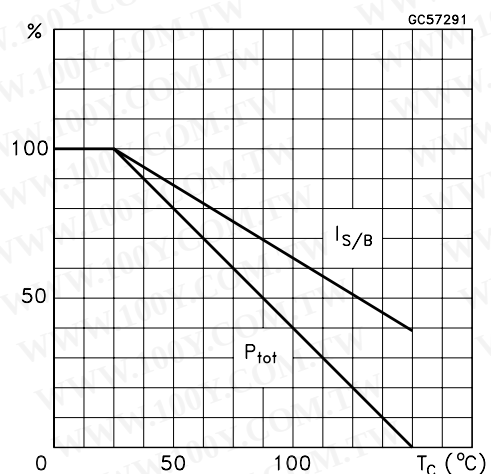
* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %.
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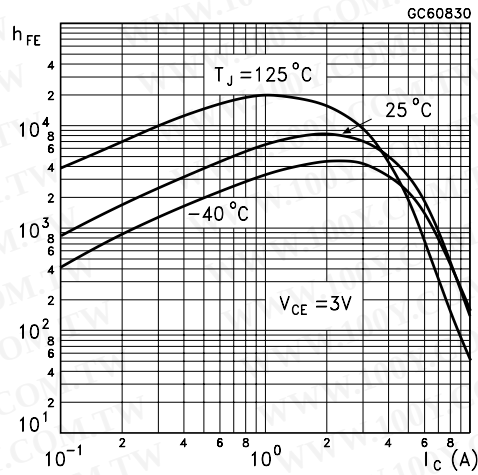
Safe Operating Area



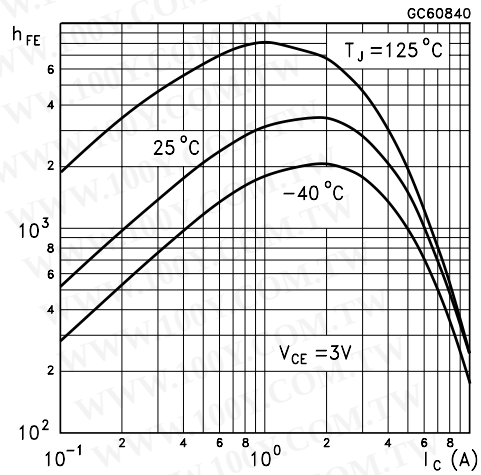
Derating Curve



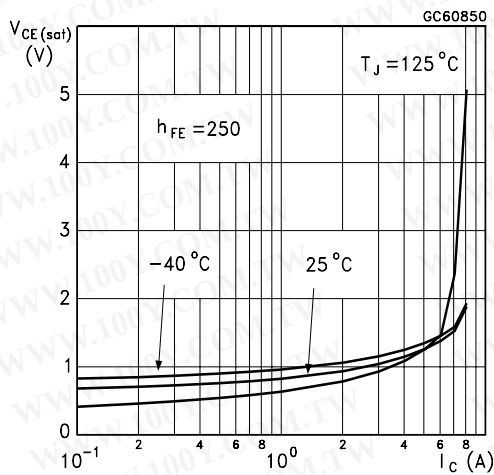
DC Current Gain (NPN type)



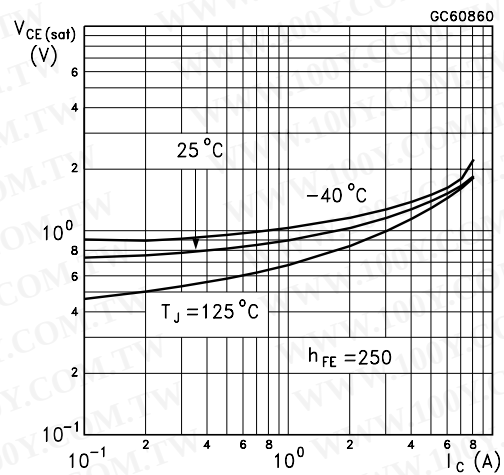
DC Current Gain (PNP type)



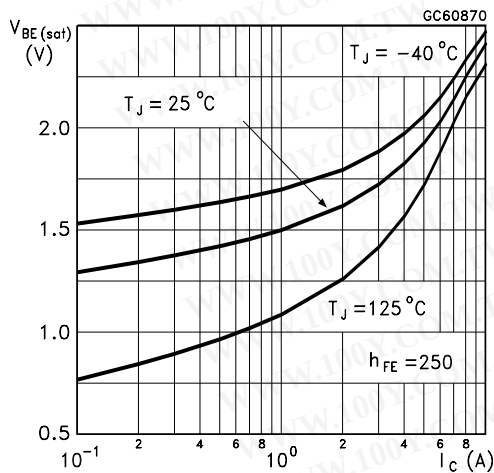
Collector Emitter Saturation Voltage (NPN type)



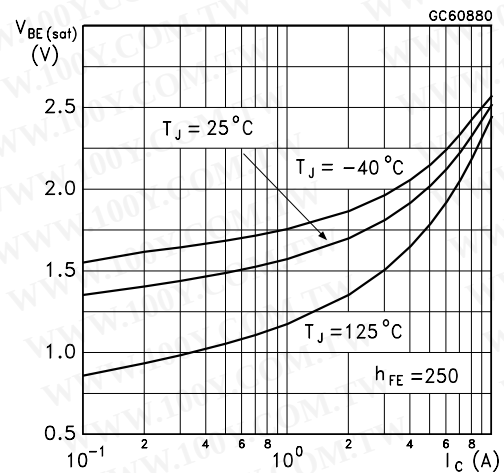
Collector Emitter Saturation Voltage (PNP type)



Base Emitter Saturation Voltage (NPN type)

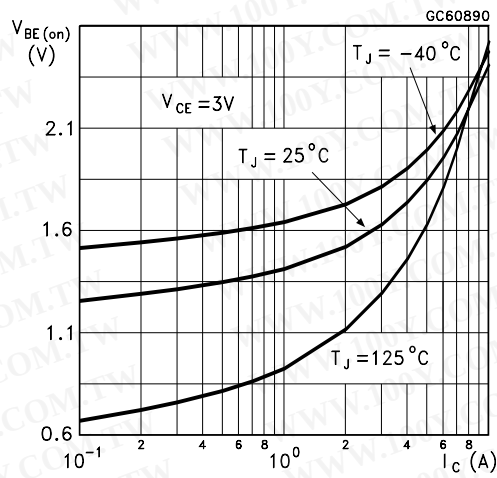


Base Emitter Saturation Voltage (PNP type)

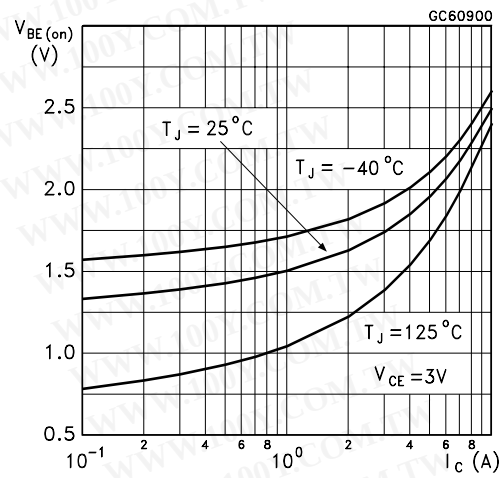


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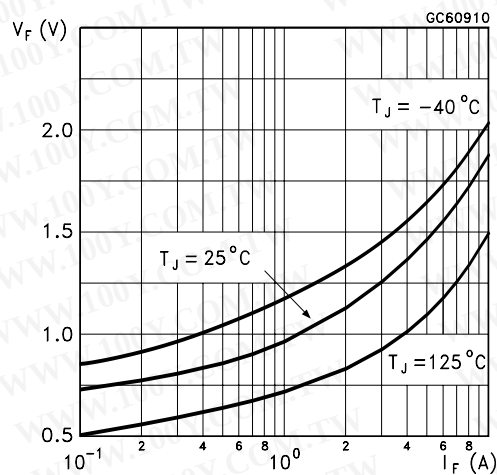
Base Emitter On Voltage (NPN type)



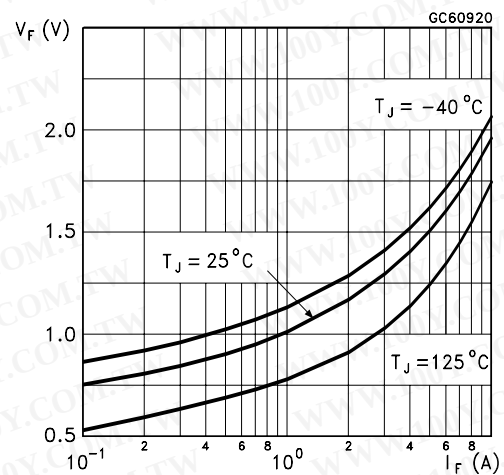
Base Emitter On Voltage (PNP type)



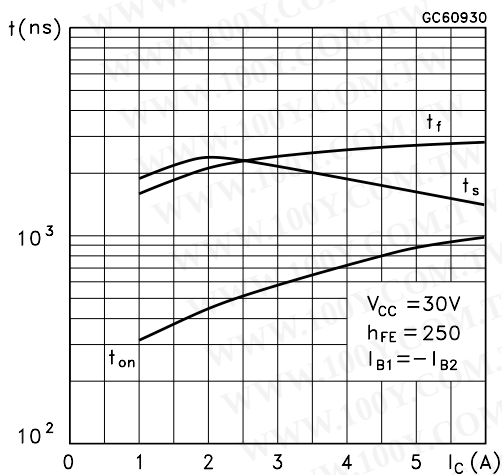
Freewheel Diode Forward Voltage (NPN type)



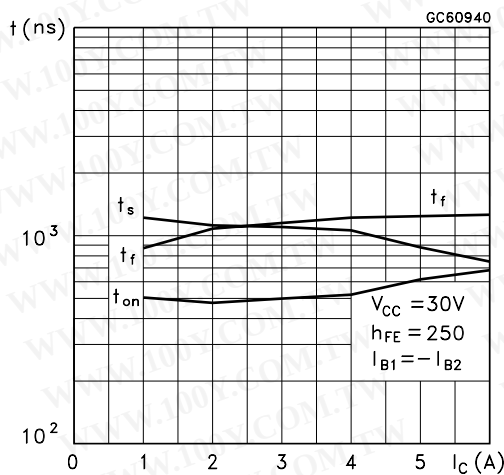
Freewheel Diode Forward Voltage (PNP type)



Switching Time Resistive Load (NPN type)

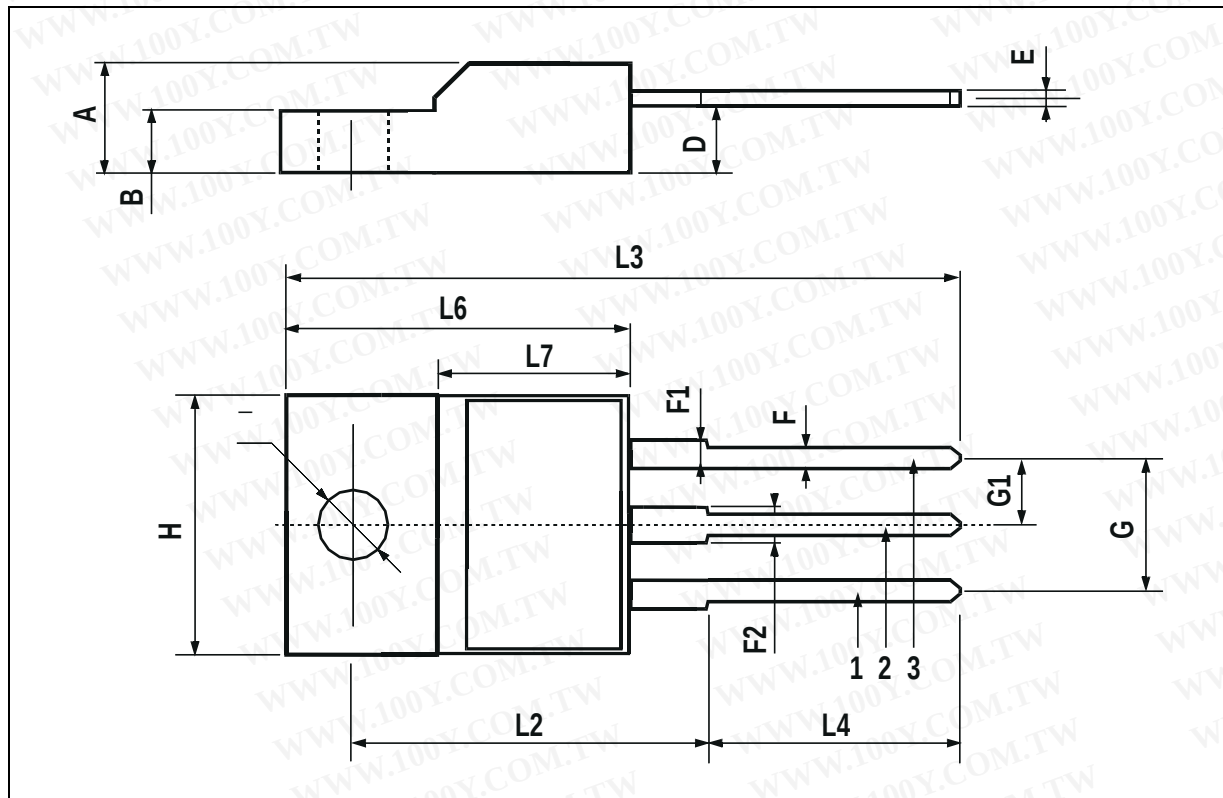


Switching Time resistive Load (PNP type)



TO-220FP MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



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